thickness described in the embodying aspect described earlier. This film is formed to a thickness that is greater than the thickness of the organic semiconductor film 43. If the organic semiconductor film 41 is formed to a thickness of 0.05 μm to 0.2 μm, for example, the film of inorganic material is formed to a thickness of approximately 0.2 μm to 1.0 μm.

Page 81, line 17 through Page 82, line 4, delete current paragraph and insert therefore:

Upper layer side insulating film formation process (Fig. 17A - 17C): A resist (upper layer side insulating film 62) is then formed along the scanning line GATE and the data line SIG. This upper layer side insulating film 62 is configured of the organic material of the embodying aspect described earlier. The thickness of the upper layer side insulating film 62 is formed to a height wherewith it can become a bulwark of such extent that the liquid thin film material will not overflow into the adjacent pixel areas even when the pixel area is filled with the liquid thin film material. If the organic semiconductor film 43 is formed to a thickness of 0.05 μm to 0.2 μm, or example, the upper layer side insulating film 62 is formed to a height of 1 μm to 2 μm or so.

IN THE CLAIMS:

Please cancel claims 13, 14 and 19-80 without prejudice or disclaimer of the subject matter contained therein. Please replace claims 1-12 and 13-18 as follows:

1. (Twice Amended) A method for manufacturing athin film patterning substrate, comprising:

providing a substrate;

forming banks on a surface of said substrate so as to form a plurality of areas partitioned by said banks, each of which has a width of a (μm) and a height of c (μm);

providing a ink-jet droplets of a liquid material in said areas to form a thin film layer, said ink-jet droplets having a diameter of d (μm),

wherein said banks and said ink-jet droplets satisfy a relationship $d/2 < b < 5d$.

2. (Twice Amended) A method for manufacturing a thin film patterning substrate according to claim 1, said banks being formed so as to satisfy relationship $a > d/4$.

3. (Three Times Amended) A method for manufacturing a thin film patterning substrate according to claim 1, said banks being formed to satisfy a relationship $c > t_0$ (where $t_0$ (μm) is film thickness of the thin film layer).

4. (Three Times Amended) A method for manufacturing a thin film patterning substrate according to claim 1, said banks being formed so as to satisfy relationship $c > d/2b$.

5. (Three Times Amended) A method for manufacturing a thin film patterning substrate according to claim 1, further comprising: at least upper surfaces of said banks being formed of an organic substance.

6. (Three Times Amended) A method for manufacturing a thin film patterning substrate according to claim 1, further comprising: upper surfaces and side surfaces of said banks being formed of an organic substance.

7. (Three Times Amended) A method for manufacturing a thin film patterning substrate according to claim 1, further comprising: forming said banks in two layers including a lower-layer inorganic substance and an upper-layer organic substance.

8. (Twice Amended) A method for manufacturing a thin film patterning substrate according to claim 7, further comprising: forming said banks in two layers including a lower-layer inorganic substance and an upper-layer organic substance, and at least side surfaces of said inorganic substance are not covered by said organic substance.

9. (Three Times Amended) A method for manufacturing a thin film patterning substrate according to claim 1, further comprising: said areas to be coated being an inorganic substance.

10. (Three Times Amended) A method for manufacturing a thin film patterning substrate according to claim 1, further comprising: upper surfaces of upper portions of said banks having liquid droplet reservoir structures.

11. (Three Times Amended) A method for manufacturing a thin film patterning substrate according to claim 5, further comprising: performing surface treatment so that an angle of contact of the organic substance surface forming said banks is 50° or greater, an angle of contact with the inorganic substance forming said banks is 20° to 50°, and an angle of contact of surfaces of said areas to be coated with said thin film liquid material is 30° or greater.

12. (Twice Amended) A method for manufacturing a thin film patterning substrate according to claim 11, further comprising: effecting said surface modification by plasma treatment.

15. (Twice Amended) A method for manufacturing a thin film patterning substrate according to claim 1, said thin film layers being organic EL elements.

16. (Twice Amended) A method for manufacturing a thin film patterning substrate according to claim 1, said thin film layers being color filters.

17. (Three Times Amended) A method for manufacturing a display device, the display device including a thin film patterning substrate, the method comprising:

providing a substrate;

forming banks on a surface of said substrate so as to form a plurality of areas partitioned by said banks, each of which has a width of a (μm) and a height of c (μm);

providing a ink-jet droplets of a liquid material in said areas to form a thin film layer, said ink-jet droplets having a diameter of d (μm),

wherein said banks and said ink-jet droplets satisfy a relationship $d/2<b<5d$.